STW7NA100
STH7NA100FI

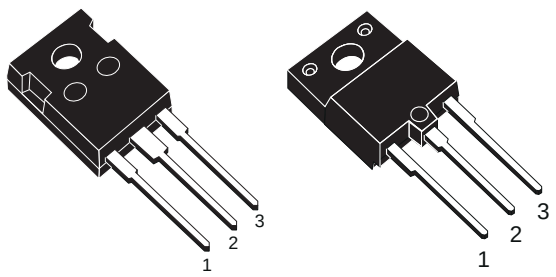
N - CHANNEL ENHANCEMENT MODE POWER MOS TRANSISTORS

TYPE	V_{DSS}	$R_{DS(on)}$	I_D
STW7NA100	1000 V	< 1.7 Ω	7 A
STH7NA100FI	1000 V	< 1.7 Ω	4.3 A

- TYPICAL $R_{DS(on)}$ = 1.45 Ω
- ± 30V GATE TO SOURCE VOLTAGE RATING
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- GATE CHARGE MINIMISED
- REDUCED THRESHOLD VOLTAGE SPREAD

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLY (SMPS)
- DC-AC CONVERTERS FOR WELDING EQUIPMENT AND UNINTERRUPTIBLE POWER SUPPLIES AND MOTOR DRIVE



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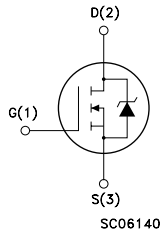
INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STW7NA100	STH7NA100FI	
V_{DS}	Drain-source Voltage (V_{GS} = 0)	1000		V
V_{DGR}	Drain- gate Voltage (R_{GS} = 20 kΩ)	1000		V
V_{GS}	Gate-source Voltage	± 30		V
I_D	Drain Current (continuous) at T_c = 25 °C	7	4.3	A
I_D	Drain Current (continuous) at T_c = 100 °C	4.4	2.7	A
I_{DM}(•)	Drain Current (pulsed)	28	28	A
P_{tot}	Total Dissipation at T_c = 25 °C	190	70	W
	Derating Factor	1.52	0.56	W/°C
V_{ISO}	Insulation Withstand Voltage (DC)	—	4000	V
T_{stg}	Storage Temperature	-65 to 150		°C
T_j	Max. Operating Junction Temperature	150		°C

(•) Pulse width limited by safe operating area

THERMAL DATA

			TO-247	ISOWATT218	
$R_{thj-case}$	Thermal Resistance Junction-case	Max	0.65	1.78	$^oC/W$
$R_{thj-amb}$ $R_{thc-sink}$ T_l	Thermal Resistance Junction-ambient Thermal Resistance Case-sink Maximum Lead Temperature For Soldering Purpose	Max Typ	30 0.1 300		$^oC/W$ $^oC/W$ ^oC

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max, $\delta < 1\%$)	7	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25\ ^oC$, $I_D = I_{AR}$, $V_{DD} = 50$ V)	800	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25\ ^oC$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250\ \mu A$ $V_{GS} = 0$	1000			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	V_{DS} = Max Rating V_{DS} = Max Rating $T_c = 100\ ^oC$			50 250	µA µA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 30$ V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250\ \mu A$	2.25	3	3.75	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 3.5$ A		1.45	1.7	Ω Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10$ V	7			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs} (*)	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 3.5$ A	5	7		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25$ V f = 1 MHz $V_{GS} = 0$		3170 270 76	4100 351 99	pF pF pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	V_{DD} = 500 V I_D = 3.5 A R_G = 4.7 Ω V_{GS} = 10 V		28 19	40 27	ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	V_{DD} = 800 V I_D = 7 A V_{GS} = 10 V		125 17 58	150	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	V_{DD} = 800 V I_D = 7A R_G = 4.7 Ω V_{GS} = 10 V		35 15 55	50 21 77	ns ns ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(•)	Source-drain Current Source-drain Current (pulsed)				7 28	A A
V_{SD} (∗)	Forward On Voltage	I_{SD} = 7 A V_{GS} = 0			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	I_{SD} = 7 A di/dt = 100 A/µs V_{DD} = 100 V T_j = 150 °C		835 14 33		ns µC A

(∗) Pulsed: Pulse duration = 300 µs, duty cycle 1.5 %
(•) Pulse width limited by safe operating area